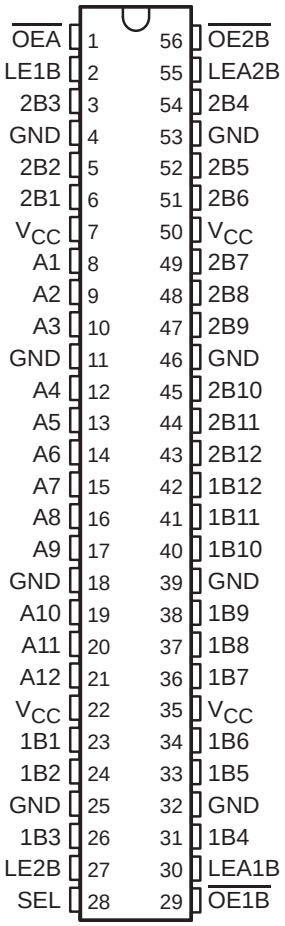
- **Members of the Texas Instruments *Widebus*™ Family**
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **High-Impedance State During Power Up and Power Down**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) Package and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54ABT16260 . . . WD PACKAGE
SN74ABTH16260 . . . DL PACKAGE
(TOP VIEW)



description

The SN54ABT16260 and SN74ABTH16260 are 12-bit to 24-bit multiplexed D-type latches used in applications in which two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing of address and data information in microprocessor or bus-interface applications. This device is also useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus-transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

description (continued)

When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54ABT16260 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABTH16260 is characterized for operation from –40°C to 85°C.

Function Tables

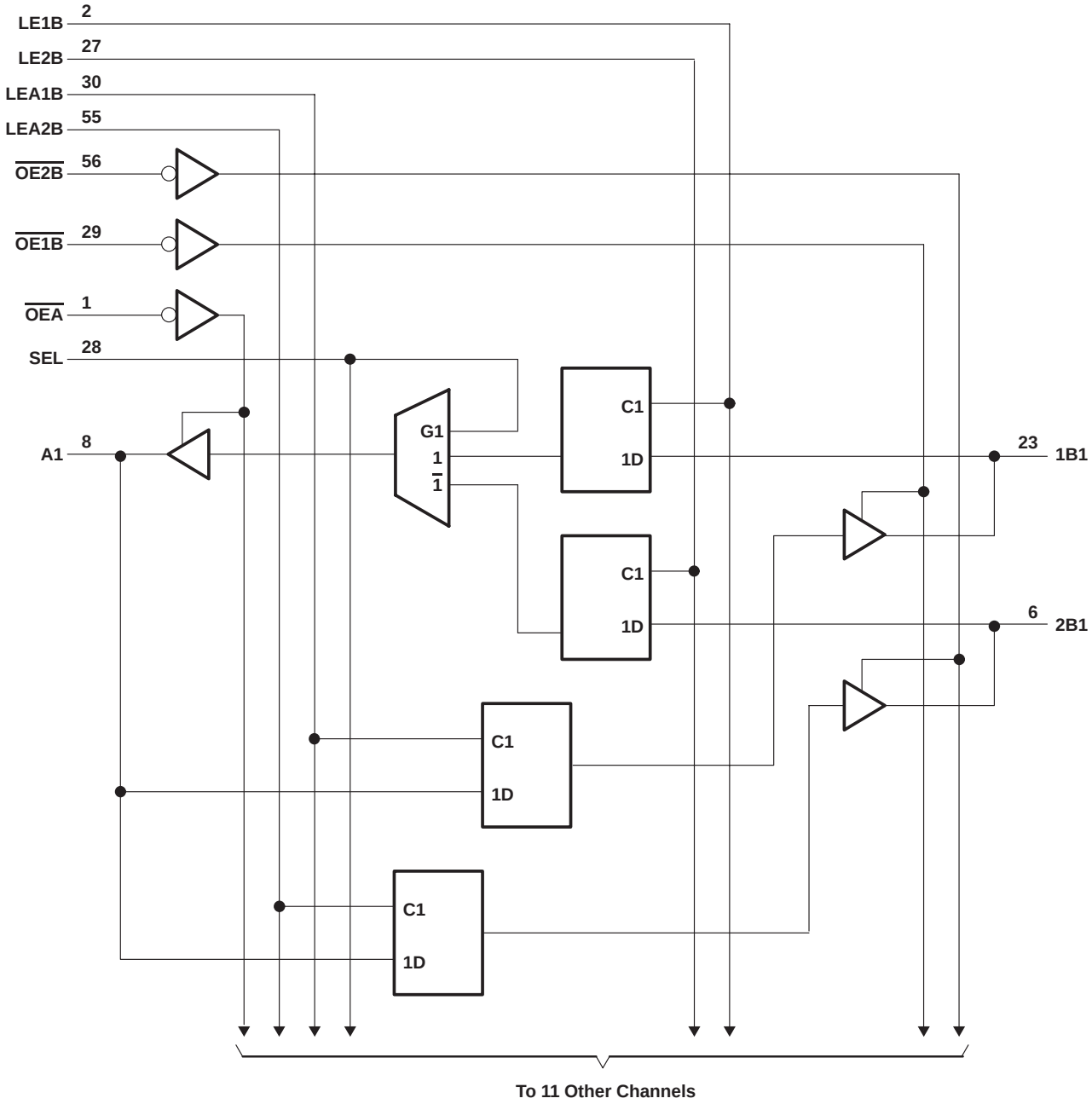
B TO A ($\overline{OEB}$ = H)

INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B ($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABT16260 . . . . . 96 mA
SN74ABTH16260 . . . . . 128 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 3)

			SN54ABT16260		SN74ABTH16260		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT16260		SN74ABTH16260		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
V_{OL}		V_{CC} = 4.5 V	I_{OL} = 48 mA		0.36			0.5			V
			I_{OL} = 64 mA			0.55*				0.55	
V_{hys}					100						mV
I_I	Control inputs	V_{CC} = 0 to 5.5 V, V_I = V_{CC} or GND				±1		±1		±1	µA
	A or B ports	V_{CC} = 2.1 V to 5.5 V, V_I = V_{CC} or GND				±20		±100		±20	
$I_{I(hold)}$	A or B ports	V_{CC} = 4.5 V	V_I = 0.8 V				100		100		µA
			V_I = 2 V				–100		–100		
I_{OZPU}‡		V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50		±50		±50	µA
I_{OZPD}‡		V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50		±50		±50	µA
I_{OZH}§		V_{CC} = 2.1 V to 5.5 V, V_O = 2.7 V, $\overline{OE}$ ≥ 2 V				10		10		10	µA
I_{OZL}§		V_{CC} = 2.1 V to 5.5 V, V_O = 0.5 V, $\overline{OE}$ ≥ 2 V				–10		–10		–10	µA
I_{off}		V_{CC} = 0,	V_I or V_O ≤ 4.5 V			±100				±100	µA
I_{CEX}		V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O¶		V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–100	–225	–50	–225	–50	–225	mA
I_{CC}		V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			1.5		1.5		1.5	mA
			Outputs low			63		63		63	
			Outputs disabled			1		1		1	
ΔI_{CC}#		V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	mA
C_i		V_I = 2.5 V or 0.5 V			3						pF
C_{io}		V_O = 2.5 V or 0.5 V			11.5						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
† All typical values are at V_{CC} = 5 V.
‡ This parameter is characterized, but not production tested.
§ The parameters I_{OZH} and I_{OZL} include the input leakage current.
¶ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

		V_{CC} = 5 V, T_A = 25°C†		SN54ABT16260		SN74ABTH16260		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B↓	1.5		2		1.5		ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B↓	1		1.5		1		ns

† These values apply only to the SN74ABTH16260.

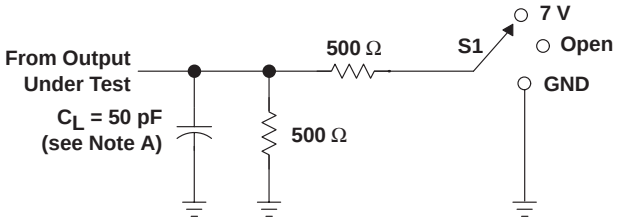
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ABT16260					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
t_{PLH}	A or B	B or A	1	3.1	5.3	1	5.9	ns
t_{PHL}			1	3.4	5.4	1	6.3	
t_{PLH}	LE	A or B	1.1	3.2	5.4	1.1	6.6	ns
t_{PHL}			1.1	3.3	5.3	1.1	5.9	
t_{PLH}	SEL (B1)	A	1.3	3.2	5.1	1.3	5.4	ns
	SEL (B2)		1.1	3.4	5.4	1.1	6.3	
t_{PHL}	SEL (B1)		1.5	3.1	4.6	1.5	5	
	SEL (B2)		1.6	3.6	5.3	1.6	6.2	
t_{PZH}	$\overline{OE}$	A or B	1	3.3	5.6	1	6.4	ns
t_{PZL}			1.6	3.8	5.9	1.6	6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.2	4.1	5.9	2.2	7.5	ns
t_{PLZ}			1.3	3.2	5	1.3	5.4	

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

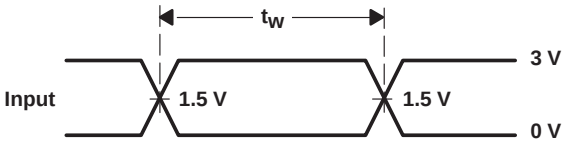
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74ABTH16260					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
t_{PLH}	A or B	B or A	1	3.1	4.8	1	5.6	ns
t_{PHL}			1	3.4	5	1	5.9	
t_{PLH}	LE	A or B	1.1	3.2	4.9	1.1	5.8	ns
t_{PHL}			1.1	3.3	4.9	1.1	5.3	
t_{PLH}	SEL (B1)	A	1.3	3.2	4.6	1.3	5.3	ns
	SEL (B2)		1.1	3.4	4.9	1.1	6	
t_{PHL}	SEL (B1)		1.5	3.1	4.4	1.5	4.4	
	SEL (B2)		1.6	3.6	5.1	1.6	5.9	
t_{PZH}	$\overline{OE}$	A or B	1	3.3	4.7	1	5.7	ns
t_{PZL}			1.6	3.8	5.1	1.6	5.8	
t_{PHZ}	$\overline{OE}$	A or B	2.2	4.1	5.4	2.2	6.4	ns
t_{PLZ}			1.3	3.2	4.4	1.3	4.8	

PARAMETER MEASUREMENT INFORMATION

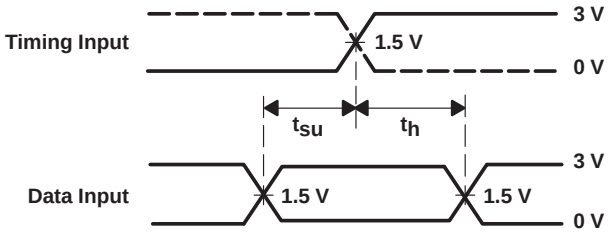


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

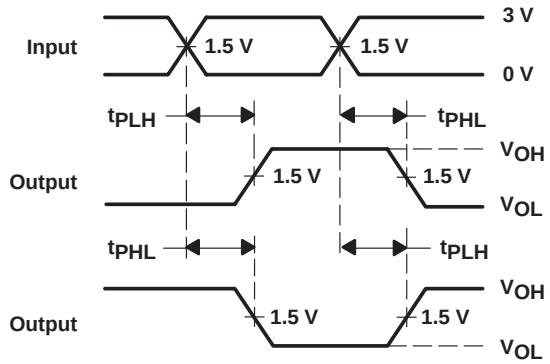
LOAD CIRCUIT



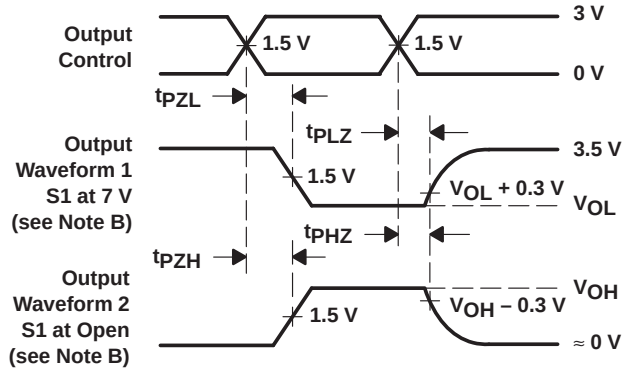
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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